ELSEVIER

Journal of Crystal Growth 203 (1999) 604–608

JOURNAL OF CRYSTAL GROWTH

# Author index

Abe, K., see Nakanishi, H. 203 (1999) 75
Adair, J.H., see Bell, N.S. 203 (1999) 213
Akane, T., M. Sano, H. Okumura, Y. Tubo, T. Ishikawa and S. Matsumoto, Characterization of gas-source molecular beam epitaxial growth of strain-compensated $Si_{1-x-y}Ge_xC_y/Si(0\,0\,1)$ heterostructure 203 (1999) 80
Alawadhi, H., see Miotkowski, I. 203 (1999) 51
Albrecht, M., see Vogg, G. 203 (1999) 570
Audinet, L., see Ricolleau, C. 203 (1999) 486

Baldochi, S.L., see Santo, A.M.E. 203 (1999) 156
Ban, V.S., see Deutsch, M. 203 (1999) 412
Becker, P., J. Liebertz and L. Bohatý, Top-seeded growth of bismuth triborate, $BiB_3O_6$ 203 (1999) 149
Bell, N.S. and J.H. Adair, Adsorbate effects on glycothermally produced α-alumina particle morphology 203 (1999) 213
Bennema, P., see Bögels, G. 203 (1999) 554
Benz, K.W., see Schweizer, M. 203 (1999) 500
Berglund, K.A., see LeCaptain, D.J. 203 (1999) 564
Berglund, K.A., see Schwartz, A.M. 203 (1999) 599
Bermúdez, V., M.D. Serrano, P.S. Dutta and E. Diéguez, Opposite domain formation in Er-doped $LiNbO_3$ bulk crystals grown by the off-centered Czochralski technique 203 (1999) 179
Bettini, J., see de Castro, M.P.P. 203 (1999) 317
Bhat, H.L., see Udayashankar, N.K. 203 (1999) 333
Binnewies, M., see Patzke, G.R. 203 (1999) 141
Bicelli, L.P., see Kozlov, V.M. 203 (1999) 255
Blant, A.V., S.V. Novikov, T.S. Cheng, L.B. Flannery, I. Harrison, R.P. Campion, D. Korakakis, E.C. Larkins, Y. Kribes and C.T. Foxon, Ga-metal inclusions in GaN grown on sapphire 203 (1999) 349
Bögels, G., J.G. Buijnsters, S.A.C. Verhaegen, H. Meekes, P. Bennema and D. Bollen, Morphology and growth mechanism of multiply twinned AgBr and AgCl needle crystals 203 (1999) 554
Bohatý, L., see Becker, P. 203 (1999) 149
Boilot, J.P., see Ricolleau, C. 203 (1999) 486
Bollen, D., see Bögels, G. 203 (1999) 554
Boufaden, T., see Rebey, A. 203 (1999) 12
Brandt, M.S., see Vogg, G. 203 (1999) 570
Buijnsters, J.G., see Bögels, G. 203 (1999) 554

Campion, R.P., see Blant, A.V. 203 (1999) 349
Carbonell, L., G. Mula and S. Tatarenko, Influence of a compressive strain on the stoichiometry of the (0 0 1)CdTe surface during molecular beam epitaxy 203 (1999) 61
Chang, J.R., Y.K. Su, D.H. Jaw, H.P. Shiao and W. Lin, Metalorganic vapor phase epitaxy (MOVPE) growth and characterization of AlInAsSb and AlInAsSb/InGaAs multiple-quantum-well structures 203 (1999) 481
Chen Huanchu, see Zhang Shujun 203 (1999) 168
Chen, Q.-S., W.-R. Hu and V. Prasad, Effect of liquid bridge volume on the instability in small-Prandtl-number half zones 203 (1999) 261
Cheng, T.S., see Blant, A.V. 203 (1999) 349
Cheng Zhenxiang, see Zhang Shujun 203 (1999) 168
Chian, J.H., see Lan, C.W. 203 (1999) 286
Chinyama, K.G., K.P. O'Donnell, A. Rosenauer and D. Gerthsen, Morphology of ultrathin CdSe quantum confinement layers in ZnSe matrices 203 (1999) 362
Christoffersen, J., see Christoffersen, M.R. 203 (1999) 234
Christoffersen, M.R., N. Seierby, T.B. Zunic and J. Christoffersen, Kinetics of dissolution of triclinic calcium pyrophosphate dihydrate crystals 203 (1999) 234
Coldren, L.A., see Hall, E. 203 (1999) 447
Cröll, A., see Schweizer, M. 203 (1999) 500

De Carvalho, M.M., see de Castro, M.P.P. 203 (1999) 317
De Castro, M.P.P., N.C. Frateschi, J. Bettini, C.A. Ribeiro and M.M. de Carvalho, Spatial composition dependence in InGaP growth on pre-patterned GaAs substrates by chemical beam epitaxy 203 (1999) 317
Deng Peizhen, see Dong Jun 203 (1999) 163
Derby, J.J., see Yeckel, A. 203 (1999) 87

0022-0248/99/$ - see front matter © 1999 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(99)00227-4

ELSEVIER

Journal of Crystal Growth 203 (1999) 604–608

JOURNAL OF CRYSTAL GROWTH

# Author index

Abe, K., see Nakanishi, H. 203 (1999) 75
Adair, J.H., see Bell, N.S. 203 (1999) 213
Akane, T., M. Sano, H. Okumura, Y. Tubo, T. Ishikawa and S. Matsumoto, Characterization of gas-source molecular beam epitaxial growth of strain-compensated $Si_{1-x-y}Ge_xC_y/Si(0\,0\,1)$ heterostructure 203 (1999) 80
Alawadhi, H., see Miotkowski, I. 203 (1999) 51
Albrecht, M., see Vogg, G. 203 (1999) 570
Audinet, L., see Ricolleau, C. 203 (1999) 486

Baldochi, S.L., see Santo, A.M.E. 203 (1999) 156
Ban, V.S., see Deutsch, M. 203 (1999) 412
Becker, P., J. Liebertz and L. Bohatý, Top-seeded growth of bismuth triborate, $BiB_3O_6$ 203 (1999) 149
Bell, N.S. and J.H. Adair, Adsorbate effects on glycothermally produced α-alumina particle morphology 203 (1999) 213
Bennema, P., see Bögels, G. 203 (1999) 554
Benz, K.W., see Schweizer, M. 203 (1999) 500
Berglund, K.A., see LeCaptain, D.J. 203 (1999) 564
Berglund, K.A., see Schwartz, A.M. 203 (1999) 599
Bermúdez, V., M.D. Serrano, P.S. Dutta and E. Diéguez, Opposite domain formation in Er-doped $LiNbO_3$ bulk crystals grown by the off-centered Czochralski technique 203 (1999) 179
Bettini, J., see de Castro, M.P.P. 203 (1999) 317
Bhat, H.L., see Udayashankar, N.K. 203 (1999) 333
Binnewies, M., see Patzke, G.R. 203 (1999) 141
Bicelli, L.P., see Kozlov, V.M. 203 (1999) 255
Blant, A.V., S.V. Novikov, T.S. Cheng, L.B. Flannery, I. Harrison, R.P. Campion, D. Korakakis, E.C. Larkins, Y. Kribes and C.T. Foxon, Ga-metal inclusions in GaN grown on sapphire 203 (1999) 349
Bögels, G., J.G. Buijnsters, S.A.C. Verhaegen, H. Meekes, P. Bennema and D. Bollen, Morphology and growth mechanism of multiply twinned AgBr and AgCl needle crystals 203 (1999) 554
Bohatý, L., see Becker, P. 203 (1999) 149
Boilot, J.P., see Ricolleau, C. 203 (1999) 486
Bollen, D., see Bögels, G. 203 (1999) 554
Boufaden, T., see Rebey, A. 203 (1999) 12
Brandt, M.S., see Vogg, G. 203 (1999) 570
Buijnsters, J.G., see Bögels, G. 203 (1999) 554

Campion, R.P., see Blant, A.V. 203 (1999) 349
Carbonell, L., G. Mula and S. Tatarenko, Influence of a compressive strain on the stoichiometry of the (0 0 1)CdTe surface during molecular beam epitaxy 203 (1999) 61
Chang, J.R., Y.K. Su, D.H. Jaw, H.P. Shiao and W. Lin, Metalorganic vapor phase epitaxy (MOVPE) growth and characterization of AlInAsSb and AlInAsSb/InGaAs multiple-quantum-well structures 203 (1999) 481
Chen Huanchu, see Zhang Shujun 203 (1999) 168
Chen, Q.-S., W.-R. Hu and V. Prasad, Effect of liquid bridge volume on the instability in small-Prandtl-number half zones 203 (1999) 261
Cheng, T.S., see Blant, A.V. 203 (1999) 349
Cheng Zhenxiang, see Zhang Shujun 203 (1999) 168
Chian, J.H., see Lan, C.W. 203 (1999) 286
Chinyama, K.G., K.P. O'Donnell, A. Rosenauer and D. Gerthsen, Morphology of ultrathin CdSe quantum confinement layers in ZnSe matrices 203 (1999) 362
Christoffersen, J., see Christoffersen, M.R. 203 (1999) 234
Christoffersen, M.R., N. Seierby, T.B. Zunic and J. Christoffersen, Kinetics of dissolution of triclinic calcium pyrophosphate dihydrate crystals 203 (1999) 234
Coldren, L.A., see Hall, E. 203 (1999) 447
Cröll, A., see Schweizer, M. 203 (1999) 500

De Carvalho, M.M., see de Castro, M.P.P. 203 (1999) 317
De Castro, M.P.P., N.C. Frateschi, J. Bettini, C.A. Ribeiro and M.M. de Carvalho, Spatial composition dependence in InGaP growth on pre-patterned GaAs substrates by chemical beam epitaxy 203 (1999) 317
Deng Peizhen, see Dong Jun 203 (1999) 163
Derby, J.J., see Yeckel, A. 203 (1999) 87

0022-0248/99/$ - see front matter © 1999 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(99)00227-4

Deutsch, M., M.C. Gerstenberg, H.F. Gossenberger, V.S. Ban and S.R. Forrest, Macroscopically ordered thin films of an organic salt grown by low-pressure organic vapor-phase deposition 203 (1999) 412
Devine, K.D., see Salinger, A.G. 203 (1999) 516
Diéguez, E., see Bermúdez, V. 203 (1999) 179
Dold, P., see Schweizer, M. 203 (1999) 500
Dong Jun, Deng Peizhen and Xu Jun, The growth of $Cr^{4+}$, $Yb^{3+}$ : yttrium aluminum garnet (YAG) crystal and its absorption spectra properties 203 (1999) 163
Doty, F.P., see Yeckel, A. 203 (1999) 87
Duan, L.H., see Xu, D.P. 203 (1999) 40
Duffy, S., J.-P.R. Wells, H.G. Gallagher and T.P.J. Han, Bridgman growth and laser excitation of $LiYF_4 : Sm^{3+}$ 203 (1999) 405
Dutta, P.S., see Bermúdez, V. 203 (1999) 179

Ebe, T., Factors determining the saturation of point defects in growing silicon crystals 203 (1999) 387
El Jani, B., see Rebey, A. 203 (1999) 12

Ferrari, C., see Jeganathan, K. 203 (1999) 327
Flannery, L.B., see Blant, A.V. 203 (1999) 349
Forrest, S.R., see Wei, J. 203 (1999) 302
Forrest, S.R., see Deutsch, M. 203 (1999) 412
Foxon, C.T., see Blant, A.V. 203 (1999) 349
Frateschi, N.C., see de Castro, M.P.P. 203 (1999) 317
Fukuda, T., see Kawaguchi, T. 203 (1999) 173

Gacoin, T., see Ricolleau, C. 203 (1999) 486
Gallagher, H.G., see Duffy, S. 203 (1999) 405
Gandais, M., see Ricolleau, C. 203 (1999) 486
Garcia, V.M., P.K. Nair and M.T.S. Nair, Copper selenide thin films by chemical bath deposition 203 (1999) 113
Gerstenberg, M.C., see Deutsch, M. 203 (1999) 412
Gerthsen, D., see Chinyama, K.G. 203 (1999) 362
Gokhale, M.R., see Wei, J. 203 (1999) 302
Goldys, E.M., see Paskova, T. 203 (1999) 1
Gopalakrishna Naik, K., see Udayashankar, N.K. 203 (1999) 333
Gossenberger, H.F., see Deutsch, M. 203 (1999) 412
Gotoh, Y., see Yumoto, H. 203 (1999) 136
Grasza, K. and M. Pawlowska, Morphological instabilities in CdTe crystal growth from the vapor phase 203 (1999) 371
Griesche, J. and K. Jacobs, Reflection high-energy electron diffraction (RHEED) oscillations in phase-locked epitaxy of ZnSe 203 (1999) 45

Hall, E. and H. Kroemer, Surface morphology of GaSb grown on (1 1 1)B GaAs by molecular beam epitaxy 203 (1999) 297
Hall, E., H. Kroemer and L.A. Coldren, Improved composition control of digitally grown AlAsSb lattice-matched to InP 203 (1999) 447
Hamai, M., see Tagami, M. 203 (1999) 594
Han Jianru, see Zhang Shujun 203 (1999) 168
Han, T.P.J., see Duffy, S. 203 (1999) 405
Harrison, I., see Blant, A.V. 203 (1999) 349
Hasegawa, M., see Tanaka, M. 203 (1999) 400
Hatta, E., see Iwata, Y. 203 (1999) 125
Hayafuji, N., see Kadoiwa, K. 203 (1999) 18
Hennigan, G.L., see Salinger, A.G. 203 (1999) 516
Heuken, M., see Schwambera, M. 203 (1999) 340
Higuchi, M., T. Togi and K. Kodaira, Growth of rutile single crystals by the pulling-down method 203 (1999) 450
Hu, W.R., see Wang, W. 203 (1999) 227
Hu, W.R., see Chen, Q.S. 203 (1999) 261
Hutchinson, S.A., see Salinger, A.G. 203 (1999) 516

Imaeda, M., see Kawaguchi, T. 203 (1999) 173
Imai, M., see Sakai, Y. 203 (1999) 244
Ishikawa, T., see Akane, T. 203 (1999) 80
Iwata, Y., H. Kobayashi, S. Kikuchi, E. Hatta and K. Mukasa, In situ reflection high-energy electron diffraction (RHEED) observation of $Bi_2Te_3/Sb_2Te_3$ multilayer film growth 203 (1999) 125
Izumi, S., see Kadoiwa, K. 203 (1999) 18

Jacobs, K., see Griesche, J. 203 (1999) 45
Jaw, D.H., see Chang, J.R. 203 (1999) 481
Jeganathan, K., C. Ferrari and J. Kumar, Structural characterisation of remelt liquid phase epitaxy (LPE) grown AlGaAs heteroepitaxial layer 203 (1999) 327
Jiang, R., see Liu, S. 203 (1999) 454

Kadoiwa, K., S. Izumi, Y. Yamamoto, N. Hayafuji and T. Sonoda, Novel InGaAs contact layer growth for hetero-junction bipolar transistors (HBTs) by using the multiple group-V source molecular beam epitaxy (MBE) system 203 (1999) 18
Kaiser, Th., see Schweizer, M. 203 (1999) 500
Kaji, K., see Sakai, Y. 203 (1999) 244
Kaneko, T., see Yumoto, H. 203 (1999) 136
Karakostas, Th., see Komninou, Ph. 203 (1999) 103
Kawaguchi, T., K. Mizuuchi, T. Yoshino, M. Imaeda, K. Yamamoto and T. Fukuda, Liquid-phase epitaxial growth of Zn-doped $LiNbO_3$ thin films and optical damage resistance for second-harmonic generation 203 (1999) 173
Kikuchi, S., see Iwata, Y. 203 (1999) 125
Kim, G., see Park, B.M. 203 (1999) 67
Klemenz, C. and H.J. Scheel, Growth and properties of $Nd_{1+x}Ba_{2-x}Cu_3O_{7\pm\delta}$ whiskers and needle-like crystals 203 (1999) 534
Kobayashi, H., see Iwata, Y. 203 (1999) 125
Kodaira, K., see Higuchi, M. 203 (1999) 450

Komninou, Ph., J. Stoemenos, G. Nouet and Th. Karakostas, Gold films epitaxially grown by diffusion at the 3C–SiC/Si interface 203 (1999) 103
Korakakis, D., see Blant, A.V. 203 (1999) 349
Kozlov, V.M. and L.P. Bicelli, Influence of the nature of metals on the formation of the deposit's polycrystalline structure during electrocrystallization 203 (1999) 255
Kribes, Y., see Blant, A.V. 203 (1999) 349
Kroemer, H., see Hall, E. 203 (1999) 297
Kroemer, H., see Hall, E. 203 (1999) 447
Krukowski, S. and J.C. Tedenac, Surface diffusion contribution to dendrite sidebranching during growth of 2D Kossel crystal from the vapor 203 (1999) 269
Kumar, J., see Jeganathan, K. 203 (1999) 327

Lachab, M., see Wang, T. 203 (1999) 443
Lan, C.W. and J.H. Chian, Effects of ampoule rotation on vertical zone-melting crystal growth: steady rotation versus accelerated crucible rotation technique (ACRT) 203 (1999) 286
Larkins, E.C., see Blant, A.V. 203 (1999) 349
LeCaptain, D.J. and K.A. Berglund, The applicability of second harmonic generation for in situ measurement of induction time of selected crystallization systems 203 (1999) 564
Li, A.Z., see Lin, C. 203 (1999) 511
Li, J.B., see Xu, D.P. 203 (1999) 40
Li, S.F., see Xu, D.P. 203 (1999) 40
Li, S.-Y. and J. Zhu, Al diffusion in GaN buffer layer during the growth of GaN film 203 (1999) 473
Li, W.-J., E.-W. Shi, W.-Z. Zhong and Z.-W. Yin, Growth mechanism and growth habit of oxide crystals 203 (1999) 186
Li Zhengdong, see Yang Shangfeng 203 (1999) 425
Lichtensteiger, M., see Schweizer, M. 203 (1999) 500
Liebertz, J., see Becker, P. 203 (1999) 149
Lin, C. and A.Z. Li, The effect of strain on the miscibility gap in Ga–In–Sb ternary alloy 203 (1999) 511
Lin, W., see Chang, J.R. 203 (1999) 481
Liu, S., R. Ma, R. Jiang and F. Luo, Synthesis and structure of hydrated neodymium carbonate 203 (1999) 454
Liu, Y.C., G.S. Song, G.C. Yang and Y.H. Zhou, Icosahedral phase growth in chill cast $Ti_{68}Fe_{28}Si_4$ alloy 203 (1999) 131
Locmelis, S., see Patzke, G.R. 203 (1999) 141
Lui, P.Y., see Yoon, S.F. 203 (1999) 31
Luo, F., see Liu, S. 203 (1999) 454

Ma, R., see Liu, S. 203 (1999) 454
Maeda, S., see Nakanishi, H. 203 (1999) 75
Mao Bingwei, see Yang Shangfeng 203 (1999) 425
Matsukura, Y., see Yokoyama, M. 203 (1999) 464
Matsumoto, S., see Akane, T. 203 (1999) 80
Meekes, H., see Bögels, G. 203 (1999) 554
Miotkowska, S., see Miotkowski, I. 203 (1999) 51
Miotkowski, I., R. Vogelgesang, H. Alawadhi, M.J. Seong, A.K. Ramdas, S. Miotkowska and W. Paszkowicz, Lattice parameters and optical characterization of $Cd_{1-x}Mg_xSe$ alloys grown by vertical gradient freezing technique 203 (1999) 51
Mizuuchi, K., see Kawaguchi, T. 203 (1999) 173
Moffat, H.K., see Salinger, A.G. 203 (1999) 516
Mogi, I., see Tagami, M. 203 (1999) 594
Monemar, B., see Paskova, T. 203 (1999) 1
Morato, S.P., see Santo, A.M.E. 203 (1999) 156
Motokawa, M., see Tagami, M. 203 (1999) 594
Mukasa, K., see Iwata, Y. 203 (1999) 125
Mula, G., see Carbonell, L. 203 (1999) 61

Nair, M.T.S., see Garcia, V.M. 203 (1999) 113
Nair, P.K., see Garcia, V.M. 203 (1999) 113
Nakagawa, D., see Wang, T. 203 (1999) 443
Nakajima, K., Thickness–composition diagrams of Stranski–Krastanov mode in the GaPSb/GaP and InGaAs/GaAs systems 203 (1999) 376
Nakanishi, H., K. Nakazato, K. Abe, S. Maeda and K. Terashima, Temperature dependence of the density of molten germanium and silicon measured by a newly developed Archimedian technique 203 (1999) 75
Nakazato, K., see Nakanishi, H. 203 (1999) 75
Naritsuka, S., see Yan, Z. 203 (1999) 25
Naritsuka, S. and T. Nishinaga, Liquid-phase epitaxy (LPE) microchannel epitaxy of InP with high reproducibility achieved by predeposition of In thin layer 203 (1999) 459
Nishinaga, T., see Yan, Z. 203 (1999) 25
Nishinaga, T., see Naritsuka, S. 203 (1999) 459
Nishiyama, K., see Yumoto, H. 203 (1999) 136
Nouet, G., see Komninou, Ph. 203 (1999) 103
Novikov, S.V., see Blant, A.V. 203 (1999) 349

O'Donnell, K.P., see Chinyama, K.G. 203 (1999) 362
Ohshita, Y. and K. Watanabe, Chemical reactions determining the step-coverage quality in plasma-assisted chemical vapor deposition of titanium 203 (1999) 540
Okumura, H., see Akane, T. 203 (1999) 80

Park, B.M., G.H. Seo and G. Kim, Effects of pulling rate fluctuation on the interstitial-vacancy boundary formation in CZ-Si single crystal 203 (1999) 67
Paskova, T., E.M. Goldys and B. Monemar, Hydride vapour-phase epitaxy growth and cathodoluminescence characterisation of thick GaN films 203 (1999) 1

Pastor, R.C., Crystal growth of metal fluorides for $CO_2$ laser operation. II. Optimization of the reactive atmosphere process (RAP) choice 203 (1999) 421
Paszkowicz, W., see Miotkowski, I. 203 (1999) 51
Patzke, G.R., S. Locmelis, R. Wartchow and M. Binnewies, Chemical transport phenomena in the ZnO–$Ga_2O_3$ system 203 (1999) 141
Pawlowska, M., see Grasza, K. 203 (1999) 371
Polak, W. and K. Sangwal, Study of the geometry of KCl clusters nucleating from vapour and in aqueous solutions 203 (1999) 434
Prasad, V., see Chen, Q.-S. 203 (1999) 261

Ramdas, A.K., see Miotkowski, I. 203 (1999) 51
Ratke, L., see Stöcker, C. 203 (1999) 582
Rebey, A., T. Boufaden and B. El Jani, In situ optical monitoring of the decomposition of GaN thin films 203 (1999) 12
Ribeiro, C.A., see de Castro, M.P.P. 203 (1999) 317
Ricolleau, C., L. Audinet, M. Gandais, T. Gacoin and J.P. Boilot, 3D morphology of II–VI semiconductor nanocrystals grown in inverted micelles 203 (1999) 486
Rosenauer, A., see Chinyama, K.G. 203 (1999) 362

Sakai, S., see Wang, T. 203 (1999) 443
Sakai, Y., M. Imai, K. Kaji and M. Tsuji, Tip-splitting crystal growth observed in crystallization from thin films of poly(ethylene terephthalate) 203 (1999) 244
Sako, T., see Yumoto, H. 203 (1999) 136
Salinger, A.G., J.N. Shadid, S.A. Hutchinson, G.L. Hennigan, K.D. Devine and H.K. Moffat, Analysis of gallium arsenide deposition in a horizontal chemical vapor deposition reactor using massively parallel computations 203 (1999) 516
Sangwal, K., Kinetic effects of impurities on the growth of single crystals from solutions 203 (1999) 197
Sangwal, K., see Polak, W. 203 (1999) 434
Sano, M., see Akane, T. 203 (1999) 80
Santo, A.M.E., S.P. Morato and S.L. Baldochi, $Ni^{2+}$ distribution in $BaLiF_3$ crystals prepared by the zone-melting technique 203 (1999) 156
Scheel, H.J., see Klemenz, C. 203 (1999) 534
Schineller, B., see Schwambera, M. 203 (1999) 340
Schmitz, D., see Schwambera, M. 203 (1999) 340
Schoen, O., see Schwambera, M. 203 (1999) 340
Schwambera, M., O. Schoen, B. Schineller, D. Schmitz and M. Heuken, Investigation of GaInN films and development of double-hetero (DH) structures for blue and green light emitters 203 (1999) 340
Schwartz, A.M. and K.A. Berglund, The use of Raman spectroscopy for in situ monitoring of lysozyme concentration during crystallization in a hanging drop 203 (1999) 599
Schweizer, M., A. Cröll, P. Dold, Th. Kaiser, M. Lichtensteiger and K.W. Benz, Measurement of temperature fluctuations and microscopic growth rates in a silicon floating zone under microgravity 203 (1999) 500
Seierby, N., see Christoffersen, M.R. 203 (1999) 234
Seo, G.H., see Park, B.M. 203 (1999) 67
Seong, M.J., see Miotkowski, I. 203 (1999) 51
Serrano, M.D., see Bermúdez, V. 203 (1999) 179
Shadid, J.N., see Salinger, A.G. 203 (1999) 516
Shi, E.-W., see Li, W.-J. 203 (1999) 186
Shiao, H.P., see Chang, J.R. 203 (1999) 481
Shirahama, T., see Wang, T. 203 (1999) 443
Song, G.S., see Liu, Y.C. 203 (1999) 131
Sonoda, T., see Kadoiwa, K. 203 (1999) 18
Stöcker, C. and L. Ratke, A new 'Jackson–Hunt' model for monotectic composite growth 203 (1999) 582
Stoemenos, J., see Komninou, Ph. 203 (1999) 103
Stutzmann, M., see Vogg, G. 203 (1999) 570
Su Genbo, see Yang Shangfeng 203 (1999) 425
Su, Y.K., see Chang, J.R. 203 (1999) 481

Tagami, M., M. Hamai, I. Mogi, K. Watanabe and M. Motokawa, Solidification of levitating water in a gradient strong magnetic field 203 (1999) 594
Takei, H., see Tanaka, M. 203 (1999) 400
Tanaka, H., see Yokoyama, M. 203 (1999) 464
Tanaka, M., M. Hasegawa and H. Takei, Growth and characterization of delafossite-type $Pd(Co_{1-x}Mn_x)O_2$ ($x = 0.04, 0.11$) single crystals 203 (1999) 400
Tang Jing, see Yang Shangfeng 203 (1999) 425
Tatarenko, S., see Carbonell, L. 203 (1999) 61
Tedenac, J.C., see Krukowski, S. 203 (1999) 269
Terashima, K., see Nakanishi, H. 203 (1999) 75
Togi, T., see Higuchi, M. 203 (1999) 450
Tsuji, M., see Sakai, Y. 203 (1999) 244
Tubo, Y., see Akane, T. 203 (1999) 80

Udayashankar, N.K., K. Gopalakrishna Naik and H.L. Bhat, The influence of temperature gradient and lowering speed on the melt–solid interface shape of $Ga_xIn_{1-x}Sb$ alloy crystals grown by vertical Bridgman technique 203 (1999) 333

Verhaegen, S.A.C., see Bögels, G. 203 (1999) 554
Vogelgesang, R., see Miotkowski, I. 203 (1999) 51
Vogg, G., M.S. Brandt, M. Stutzmann and M. Albrecht, From $CaSi_2$ to siloxene: epitaxial silicide and sheet polymer films on silicon 203 (1999) 570

Wang, C.-W., Substrate misorientation effects on $Zn_{1-x}Mg_xSe$ layers grown on GaAs(1 1 1) by molecular beam epitaxy 203 (1999) 355

Wang, T., M. Lachab, D. Nakagawa, T. Shirahama and S. Sakai, Investigation of two-dimensional electron gas in AlGaN/GaN heterostructures grown by metalorganic chemical vapor deposition (MOCVD) 203 (1999) 443
Wang, W. and W.R. Hu, Concentration distribution in solution crystal growth: effect of moving interface conditions 203 (1999) 227
Wang, Y.T., see Xu, D.P. 203 (1999) 40
Wartchow, R., see Patzke, G.R. 203 (1999) 141
Watanabe, K., see Ohshita, Y. 203 (1999) 540
Watanabe, K., see Tagami, M. 203 (1999) 594
Wei, J., M.R. Gokhale and S.R. Forrest, Growth of thallium containing III–V materials by gas-source molecular beam epitaxy 203 (1999) 302
Wells, J.-P.R., see Duffy, S. 203 (1999) 405
Wright, A.C., Microstructure of zinc selenide single crystals grown by solid phase recrystallisation 203 (1999) 309
Wu Jianmin, see Yang Shangfeng 203 (1999) 425
Wu, R.H., see Xu, D.P. 203 (1999) 40

Xu, D.P., H. Yang, D.G. Zhao, J.B. Li, L.X. Zheng, Y.T. Wang, S.F. Li, L.H. Duan and R.H. Wu, Scanning electron microscope studies of cubic $Al_xGa_{1-x}N$ films grown on GaAs(1 0 0) by metal organic vapor phase epitaxy (MOVPE) 203 (1999) 40
Xu Jun, see Dong Jun 203 (1999) 163

Yamamoto, K., see Kawaguchi, T. 203 (1999) 173
Yamamoto, Y., see Kadoiwa, K. 203 (1999) 18
Yan, Z., S. Naritsuka and T. Nishinaga, Interface supersaturation in microchannel epitaxy of InP 203 (1999) 25
Yang, G.C., see Liu, Y.C. 203 (1999) 131
Yang, H., see Xu, D.P. 203 (1999) 40
Yang Shangfeng, Su Genbo, Tang Jing, Mao Bingwei, Wu Jianmin and Li Zhengdong, Surface topography of rapidly grown $KH_2PO_4$ crystals with additives: ex situ investigation by atomic force microscopy 203 (1999) 425
Yeckel, A., F.P. Doty and J.J. Derby, Effect of steady crucible rotation on segregation in high-pressure vertical Bridgman growth of cadmium zinc telluride 203 (1999) 87
Yin, Z.-W., see Li, W.-J. 203 (1999) 186
Yokoyama, M., Y. Matsukura and H. Tanaka, Selective epitaxial growth of GaAs using dimethylgalliumchloride by multi-wafer low-pressure metal organic vapor phase epitaxy (LP-MOVPE) 203 (1999) 464
Yoon, S.F., P.Y. Lui and H.Q. Zheng, Deep-level transient spectroscopy characterization of $In_{0.48}Ga_{0.52}P$ grown at different V/III ratio using a valved phosphorus cracker cell in solid source molecular beam epitaxy 203 (1999) 31
Yoshino, T., see Kawaguchi, T. 203 (1999) 173
Yumoto, H., T. Sako, Y. Gotoh, K. Nishiyama and T. Kaneko, Growth mechanism of vapor–liquid–solid (VLS) grown indium tin oxide (ITO) whiskers along the substrate 203 (1999) 136

Zeng, H.C., Purification growth of orthorhombic molybdenum trioxide crystals from alkali-metal-containing Mo-sources 203 (1999) 547
Zhang Jiguo, see Zhang Shujun 203 (1999) 168
Zhang Shujun, Zhang Jiguo, Cheng Zhenxiang, Zhou Guangyong, Han Jianru and Chen Huanchu, Studies on the growth and defects of $GdCa_4O(BO_3)_3$ crystals 203 (1999) 168
Zhao, D.G., see Xu, D.P. 203 (1999) 40
Zheng, H.Q., see Yoon, S.F. 203 (1999) 31
Zheng, L.X., see Xu, D.P. 203 (1999) 40
Zhong, W.-Z., see Li, W.-J. 203 (1999) 186
Zhou Guangyong, see Zhang Shujun 203 (1999) 168
Zhou, Y.H., see Liu, Y.C. 203 (1999) 131
Zhu, J., see Li, S.-Y. 203 (1999) 473
Zunic, T.B., see Christoffersen, M.R. 203 (1999) 234

ELSEVIER

Journal of Crystal Growth 203 (1999) 609–610

JOURNAL OF CRYSTAL GROWTH

# Subject index

Apparatus
- for containerless growth 594

Computer simulation
- of continuum transport 87
- of dendritic growth 269
- of stability analysis 261
- of vertical zone melting 286
Constitutional supercooling
- of cadmium telluride 371
- of monotectic alloys 582
Convection 286, 500, 516, 582

Dendritic growth
- of gadolinium calcium oxoborate 168
Device characterization
- diodes 103, 355
- electronic materials 412
- lasers 412
- nonlinear optics 149
- quantum wells 362
Diffusional control
- of gallium nitride 473
- of polymer crystallization 244
Diodes, see Device characterization

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
- chemical 12, 179, 317
- photolithographic 317
- thermal 12
Eutectic growth, of
- gold 103

Heat flow control, of
- vertical zone melting 286
Hydrodynamics, see Convection

Kinetics
- of dissolution 234
- of growth 40, 61, 67, 125, 186, 197, 227, 244, 317, 599
- of interface control 355
- of nucleation 412, 599

Lasers, see Device characterization
Lasers, crystals for
- barium lithium fluoride 156
- yttrium aluminum garnet 163
Lysozyme 599

Melt growth technique
- by Bridgman–Stockbarger method
- - of cadmium zinc telluride 87
- - of gallium indium antimonide 333
- - of lithium yttrium fluoride 405
- by chill cast
- - of titanium iron silicide quasicrystals 131
- by Czochralski method
- - of germanium 75
- - of lithium niobate 179
- - of silicon 67
- - of yttrium aluminum garnet 163
- by floating zone method
- - of barium lithium fluoride 156
- - of silicon 500
- by pulling down method
- - of rutile 450
- by uniaxial solidification
- - of cadmium magnesium selenide 51
- theory of
- - silicon grown in defects 387
- - stability 261
- - two-dimensional nucleation 168
Microgravity, growth under
- of magnetic levitation 594
- of silicon 500
- of sodium chloride 227
Morphological stability
- of alpha-alumina 213
- of cadmium sulphide 486
- of cadmium telluride 371
- of clusters 434
- of oxide crystals 186
- of polyethylene terephthalate 244

0022-0248/99/$ - see front matter © 1999 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(99)00228-6

Nucleation
- of cadmium sulphide 486
- of electrodeposits 255
- of potassium chloride 434
- of potassium dihydrogen phosphide 564
Numbers
- Grashof 87
- Marangoni 261, 582
- Peclet 87, 582
- Taylor 87, 286

Phase diagrams, of
- bismuth borate 149
- growth modes 376

Quantum wells, see Device characterization

Solid growth technique
- by recrystallization
- - of zinc selenide 309
Solution growth
- by electrodeposition
- - of cadmium 255
- - of copper 255
- - of nickel 255
- by extractive crystallization
- - of silver bromide 554
- - of silver chloride 554
- by flux
- - of bismuth borate 149
- - of molybdenum trioxide 547
- - of neodymium barium cuprate 534
- by hanging drop
- - of lysozyme 599
- by hydrothermal method
- - of alpha-alumina 213
- by inverted micelles
- - of cadmium sulphide 486
- by low temperature method
- - of hydrated neodymium carbonate 454
- - of potassium dihydrogen phosphate 197, 425
- by metathetical reaction
- - of palladium cobalt cuprate 400
- theory
- - of growth habit 186
Stefan problem or moving boundary problem 87, 227
Surface energy determination
- of triclinic calcium pyrophosphate dihydrate 234
Surface structure, of
- aluminum gallium nitride 40
- cadmium telluride 61, 371
- gallium nitride 349
- ionic clusters 434
- s–k growth modes 376
- silicon germanium carbon 80
- zinc selenide 45

Thin film growth, epitaxy
- by chemical bath deposition
- - of copper selenide 113
- by liquid phase epitaxy
- - of aluminum gallium arsenide 327
- - of indium phosphide 25, 459
- - of lithium niobate 173
- by metalorganic molecular beam epitaxy
- - of indium gallium phosphide 317
- by molecular beam epitaxy
- - of aluminum arsenide antimonide 447
- - of antimony telluride 125
- - of bismuth telluride 125
- - of cadmium telluride 61
- - of gallium antimonide 297
- - of gallium nitride 349
- - of indium gallium arsenide 18
- - of indium gallium phosphide 31
- - of indium gallium thallium arsenide 302
- - of indium thallium phosphide 302
- - of silicon germanium carbon 80
- - of zinc magnesium selenide 355
- - of zinc selenide 45
- by reactive deposition epitaxy
- - of calcium disilicide 570
- - of siloxene 570
- by vapor phase epitaxy
- - through chemical vapor deposition
- - - of cadmium selenide 362
- - - of gallium nitride 1, 473
- - - of titanium silicide 540
- - - of zinc selenide 362
- - through metalorganic chemical vapor deposition
- - - of aluminum gallium nitride 40, 443
- - - of aluminum indium arsenide antimonide 481
- - - of gallium arsenide 464, 516
- - - of gallium nitride 12
- - - of indium gallium nitride 340
- theory of
- - growth modes 376
- - strain induced miscibility 511

Vapor growth technique
- by chemical transport
- - of zinc gallium oxide 141
- by evaporation and condensation
- - of cadmium telluride 371
- - of organic salt 412
- by reactive atmosphere process
- - of metal fluorides 421
- theory
- - of dendritic growth 269
Vapor–liquid–solid growth
- of indium tin oxide 136

Whiskers growth
- of indium tin oxide 136
- of neodymium barium cuprate 534